AMENDMENTS TO THE CLAIMS

- (Currently Amended) Tool (7) for handling a wafer (100), particularly a semiconductor 1. material wafer, in an epitaxial growth station (1), preferably of the type with a disk shaped susceptor, the tool (7) being adapted to be applied to an arm (5) of a robot (4) for the automatic insertion/extraction of wafers into/from the reaction chamber (2) of the station (1), the arm (5) being provided with a suction duct (6) connected to a suction system (3), the tool (7) comprising: a disk (20) having an upper side (21) and a lower side (22), the lower side (22) being so shaped as to get in contact with the wafer (100) only along the edge (103) of the wafer (100), the disk (20) being provided internally with a suction chamber (24) that is in communication with the outside of the disk (20) through one or more suction holes (25) and that is adapted to be put in communication with the suction duct (6) through a suction port (26), characterized in that the disk (20) is such as to entirely cover covering the wafer (100) and in that the suction hole/ holes (25) opens/open to the lower side (22) of the disk (20), whereby, wherein when the wafer (100) is in contact with the lower side (22) of the disk (20) and the suction system (30) is active, the wafer (100) is held by the tool (7) through suction and wherein the disk, on its lower side in its central part, is provided with a suction cavity, and wherein the suction holes are open to the lower side of the disk into the suction cavity.
- 2. (Cancelled)

- 3. (Currently Amended) Tool according to claim 1 wherein the suction port (26) opens to the upper side (21) of the disk (20).
- 4. (Currently Amended) Tool according to claim 1, wherein the disk (20) comprises a shell (28), having an outline being substantially ring-shaped and cross-section being substantially U-shaped, and a lid (29), being substantially flat and being substantially circle-shaped, joined to the shell (28) in such a way as to form a closed chaniber chamber (24) corresponding to the suction chamber and a cavity (27) being substantially cylinder-shaped and corresponding to the suction cavity, and wherein the shell (28) is so shaped as to get in contact with the wafer (100) only along the edge (103) of the wafer (100).
- 5. (Currently Amended) Tool according to claim 4, wherein the suction holes (25) open to the lateral walls of the cylinder-shaped cavity (27).
- 6. (Currently Amended) Tool according to claim 4, wherein the suction holes (25) consist of grooves made on the inner lip of the shell (28) at the border with the lid (29).
- 7. (Currently Amended) Tool according to claim 1, wherein the disk (20) is provided with a plate (23) for applying the tool (7) to the arm (5) of the robot (4), and wherein the suction port (26) opens to or next to the plate (23).

- 8. (Currently Amended) Tool according to claim 4, wherein the lid (29) is provided with a plate (23) for applying the tool (7) to the arm (5) of the robot (4), and wherein the suction port (26) opens to or next to the plate (23).
- (Currently Amended) Station for epitaxial growth treatment of wafers, particularly 9. semiconductor material wafers, comprising a reaction chamber (2), a suction system (3) and a robot (4) for the automatic insertion/extraction of wafers into/from the reaction chamber (2), the robot (4) being provided with an ann arm (5) having a suction duct (6) connected to the suction system (3), characterized in that it comprises a tool, (7) according to any of the preceding claims provided with a suction chamber (24) and adapted to handle a wafer (100), the tool (7) being applied to the arm (5) of the robot (4) and the suction chamber (24) being in communication with the suction duct (6) the tool being adapted to be applied to an arm of a robot for the automatic insertion/extraction of wafers into/from the reaction chamber of the station the arm being provided with a suction duct connected to a suction system the tool comprising: a disk having an upper side and a lower side the lower side being so shaped as to get in contact with the wafer only along the edge of the wafer the disk being provided internally with a suction chamber that is in communication with the outside of the disk through suction holes and that is adapted to be put in communication with the suction duct through a suction port the disk entirely covering the wafer wherein when the wafer is in contact with the lower side of the disk and the suction system is active, the wafer is held by the tool through suction and wherein the disk, on its lower side in

its central part, is provided with a suction cavity, and wherein the suction holes are open to the lower side of the disk into the suction cavity.

- 10. (Currently Amended) Station according to claim 9, wherein the reaction chamber (2) is of the type with a disk-shaped susceptor (9).
- 11. (Currently Amended) Station according to claim 9 wherein the arm (5) of the robot (4) essentially consists of a tube (6) that also acts as suction duct.
- 12. (Currently Amended) Station according to claim 11, wherein the arm (5) of the robot (4) comprises a plate (10), joined to one end of the tube (6), adapted to be applied to the tool (7), particularly to the plate (23) of the tool (7), and provided with an internal duct (11) that puts the tube (6) of the arm (5) in communication with the suction port (26) of the disk (20).
- 13. (Currently Amended) Station according to claim 9, wherein the reaction chamber (2) houses a support (9) that is provided with at least one pocket (12) for seating a wafer to be treated (200) in the station (1), the pocket (12) consisting of a first cavity (121) and a second cavity (122) formed within the first cavity (121) and having a substantially fiat bottom and having a shape and a size corresponding to the wafer to be treated.
- 14. (Currently Amended) Station according to claim 13, wherein the dept of the second cavity (122) is smaller than the width of the wafer (200) to be treated.

- 15. (Currently Amended) Station according to claim 13, wherein the overall depth of the first cavity (121) and of the second cavity (122) is larger than the width of the wafer (200) to be treated.
- 16. (Currently Amended) Station according to claim 9, wherein the suction system (3) is adapted to realize a suction that depends on the wafer handling phase.
- 17. (Currently Amended) Station according to claim 16, comprising an inlet area (13) for wafers to be treated, an outlet area (13) for wafers already treated, and a treatment area (2), wherein the suction system (3) is adapted to realize:
- a suction of a first value during a phase of transferring a wafer from the inlet area (13) to the treatment area (2) and during a phase of transferring a wafer from the treatment area (2) to the outlet area (13),
- a suction of a second value during a phase of picking up a wafer from the inlet area (13),
- a suction of a third value during a phase of picking up a wafer from the treatment area (2), and wherein the third value is bigger than the second value and the second value is bigger than the first value.
- 18. (Currently Amended) Station according to claim 9, wherein the suction system (3) is adapted to cause such a pressure depression in the space between the disk (20) and the handled wafer (100) as to cause no damage to the structure or to the surfaces of the handled wafer (100).

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- 19. (Currently Amended) Station according to claim 9, wherein, the suction system (3) is of the type operating by Venturi effect.
- 20. (Currently Amended) Station according to claim 19, wherein the suction system (3) comprises a programmable Mass Flow Controller for [MEC] controlling the flow of inert gas.
- 21. (New) Tool according to claim 1, wherein the suction holes open laterally into the suction cavity.